# Noninverting Buffer / CMOS Logic Level Shifter with LSTTL-Compatible Inputs

The MC74VHCT50A is a hex noninverting buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

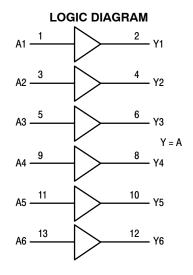
The internal circuit is composed of three stages, including a buffered output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS Logic or from 1.8 V CMOS logic to 3.0 V CMOS Logic while operating at the high-voltage power supply.

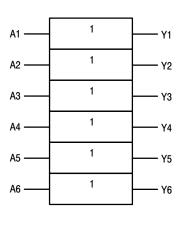
The MC74VHCT50A input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHCT50A to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when  $V_{\rm CC} = 0$  V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

## **Features**

- High Speed:  $t_{PD} = 3.5 \text{ ns}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 2 \mu A \text{ (Max)}$  at  $T_A = 25^{\circ}\text{C}$
- TTL-Compatible Inputs:  $V_{IL} = 0.8 \text{ V}$ ;  $V_{IH} = 2.0 \text{ V}$
- CMOS–Compatible Outputs:  $V_{OH} > 0.8 V_{CC}$ ;  $V_{OL} < 0.1 V_{CC}$  @Load
- Power Down Protection Provided on Inputs and Outputs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant



# LOGIC SYMBOL





# ON Semiconductor®

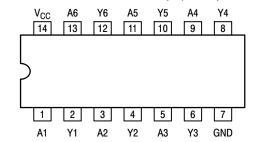
http://onsemi.com





14-LEAD SOIC D SUFFIX CASE 751A 14-LEAD TSSOP DT SUFFIX CASE 948G

# PIN CONNECTION AND MARKING DIAGRAM (Top View)



For detailed package marking information, see the Marking Diagram section on page 4 of this data sheet.

# **FUNCTION TABLE**

| A Input | Y Output |
|---------|----------|
| Г       | L        |
| Н       | Н        |

### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

## **MAXIMUM RATINGS**

| Symbol                |                                  | Parameter  | Value                      | Unit |
|-----------------------|----------------------------------|--|----------------------------|------|
| V <sub>CC</sub>       | DC Supply Voltage                |  | -0.5 to +7.0               | V    |
| V <sub>IN</sub>       | DC Input Voltage                 |  | $-0.5 \le V_{  } \le +7.0$ | V    |
| V <sub>OUT</sub>      | DC Output Voltage                | Output in HIGH or LOW State  | $-0.5 \le V_{O} \le +7.0$  | V    |
| I <sub>IK</sub>       | DC Input Diode Current           |  | -20                        | mA   |
| I <sub>OK</sub>       | DC Output Diode Current          |  | ±20                        | mA   |
| I <sub>O</sub>        | DC Output Source/Sink Current    |  | ±25                        | mA   |
| I <sub>CC</sub>       | DC Supply Current per Supply Pin |  | ±50                        | mA   |
| I <sub>GND</sub>      | DC Ground Current per Ground Pin |  | ±50                        | mA   |
| T <sub>STG</sub>      | Storage Temperature Range        |  | -65 to +150                | °C   |
| TL                    | Lead Temperature, 1 mm from Case | for 10 Seconds   | 260                        | °C   |
| TJ                    | Junction Temperature under Bias  |  | + 150                      | °C   |
| $\theta_{\sf JA}$     | Thermal Resistance               | (Note 1)<br>SOIC<br>TSSOP  | 125<br>170                 | °C/W |
| P <sub>D</sub>        | Power Dissipation in Still Air   | SOIC<br>TSSOP  | 500<br>450                 | mW   |
| V <sub>ESD</sub>      | ESD Withstand Voltage            | Human Body Model (Note 2)<br>Machine Model (Note 3)<br>Charged Device Model (Note 4) | > 2000<br>> 200<br>2000    | V    |
| I <sub>Latch-Up</sub> | Latch-Up Performance             | Above V <sub>CC</sub> and Below GND at 85°C (Note 5)                                 | ±300                       | mA   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- Tested to EIA/JESD78.

# RECOMMENDED OPERATING CONDITIONS

| Characteristics   | Symbol                          | Min        | Max                    | Unit |
|---|---------------------------------|------------|------------------------|------|
| DC Supply Voltage   | V <sub>CC</sub>                 | 2.0        | 5.5                    | V    |
| DC Input Voltage  | V <sub>IN</sub>                 | 0.0        | 5.5                    | V    |
| DC Output Voltage $V_{CC} = 0$ High or Low State  | V <sub>OUT</sub>                | 0.0<br>0.0 | 5.5<br>V <sub>CC</sub> | V    |
| Operating Temperature Range   | T <sub>A</sub>                  | -55        | +125                   | °C   |
| Input Rise and Fall Time $ \begin{array}{c} V_{CC} = 3.3 \ V \pm 0.3 \ V \\ V_{CC} = 5.0 \ V \pm 0.5 \ V \\ \end{array} $ | t <sub>r</sub> , t <sub>f</sub> | 0<br>0     | 100<br>20              | ns/V |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

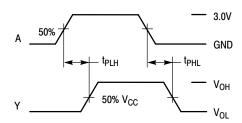
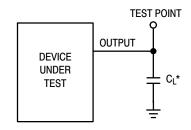


Figure 1. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 2. Test Circuit

# DC ELECTRICAL CHARACTERISTICS

|                  |   |  | V <sub>CC</sub>   | ٦                 | Γ <sub>A</sub> = 25°( | )                  | T <sub>A</sub> ≤  | 85°C               | <b>T</b> <sub>A</sub> ≤ 1 | 125°C              |      |
|------------------|---|--|-------------------|-------------------|-----------------------|--------------------|-------------------|--------------------|---------------------------|--------------------|------|
| Symbol           | Parameter   | Test Conditions  | (V)               | Min               | Тур                   | Max                | Min               | Max                | Min                       | Max                | Unit |
| V <sub>IH</sub>  | Minimum High-Level<br>Input Voltage   |  | 3.0<br>4.5<br>5.5 | 1.2<br>2.0<br>2.0 |                       |                    | 1.2<br>2.0<br>2.0 |                    | 1.2<br>2.0<br>2.0         |                    | V    |
| V <sub>IL</sub>  | Maximum Low-Level<br>Input Voltage  |  | 3.0<br>4.5<br>5.5 |                   |                       | 0.53<br>0.8<br>0.8 |                   | 0.53<br>0.8<br>0.8 |                           | 0.53<br>0.8<br>0.8 | ٧    |
| V <sub>OH</sub>  | Minimum High-Level<br>Output Voltage  | $V_{IN} = V_{IH}$ or $V_{IL}$<br>$I_{OH} = -50 \mu A$  | 3.0<br>4.5        | 2.9<br>4.4        | 3.0<br>4.5            |                    | 2.9<br>4.4        |                    | 2.9<br>4.4                |                    | V    |
|                  | $V_{IN} = V_{IH}$ or $V_{IL}$   | $V_{IN} = V_{IH}$ or $V_{IL}$<br>$I_{OH} = -4$ mA<br>$I_{OH} = -8$ mA  | 3.0<br>4.5        | 2.58<br>3.94      |                       |                    | 2.48<br>3.80      |                    | 2.34<br>3.66              |                    | ٧    |
| V <sub>OL</sub>  | Maximum Low-Level<br>Output Voltage<br>V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> | $V_{IN} = V_{IH}$ or $V_{IL}$<br>$I_{OL} = 50 \mu A$   | 3.0<br>4.5        |                   | 0.0<br>0.0            | 0.1<br>0.1         |                   | 0.1<br>0.1         |                           | 0.1<br>0.1         | V    |
|                  |   | $\begin{split} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OH} = -4 \text{ mA} \\ &I_{OL} = 8 \text{ mA} \end{split}$ | 3.0<br>4.5        |                   |                       | 0.36<br>0.36       |                   | 0.44<br>0.44       |                           | 0.52<br>0.52       | ٧    |
| I <sub>IN</sub>  | Maximum Input<br>Leakage Current  | V <sub>IN</sub> = 5.5 V or GND   | 0 to<br>5.5       |                   |                       | ±0.1               |                   | ±1.0               |                           | ±1.0               | μА   |
| I <sub>CC</sub>  | Maximum Quiescent<br>Supply Current   | V <sub>IN</sub> = V <sub>CC</sub> or GND   | 5.5               |                   |                       | 2.0                |                   | 20                 |                           | 40                 | μА   |
| I <sub>CCT</sub> | Quiescent Supply<br>Current   | Input: V <sub>IN</sub> = 3.4 V   | 5.5               |                   |                       | 1.35               |                   | 1.50               |                           | 1.65               | mA   |
| I <sub>OFF</sub> | Output Leakage<br>Current   | V <sub>OUT</sub> = 5.5 V   | 0.0               |                   |                       | 0.5                |                   | 5.0                |                           | 10                 | μА   |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# AC ELECTRICAL CHARACTERISTICS ( $C_{load} = 50 \text{ pF}$ , Input $t_r = t_f = 3.0 \text{ns}$ )

|  |                              |                                  |  | 7   | Γ <sub>A</sub> = 25°( | )           | T <sub>A</sub> ≤ | 85°C        | <b>T</b> <sub>A</sub> ≤ 1 | 125°C       |      |
|--|------------------------------|----------------------------------|--|-----|-----------------------|-------------|------------------|-------------|---------------------------|-------------|------|
| Symbol                                 | Parameter                    | Test Condi                       | tions  | Min | Тур                   | Max         | Min              | Max         | Min                       | Max         | Unit |
| t <sub>PLH</sub> ,<br>t <sub>PHL</sub> | Maximum Propogation Delay,   | $V_{CC} = 3.3 \pm 0.3 \text{ V}$ | $C_L = 15 \text{ pF}$<br>$C_L = 50 \text{ pF}$ |     | 5.5<br>8.0            | 7.9<br>11.4 | 1.0<br>1.0       | 9.5<br>13.0 |                           |             | ns   |
|  | Input A to Y                 | $V_{CC} = 5.0 \pm 0.5 \text{ V}$ | $C_L = 15 pF$<br>$C_L = 50 pF$                 |     | 6.2<br>7.0            | 7.5<br>8.5  |                  | 8.5<br>9.5  |                           | 9.5<br>10.5 |      |
| C <sub>IN</sub>                        | Maximum Input<br>Capacitance |                                  |  |     | 5                     | 10          |                  | 10          |                           | 10          | pF   |

|                 |  | Typical @ 25°C, V <sub>CC</sub> = 5.0 V |    |
|-----------------|--|---|----|
| C <sub>PD</sub> | Power Dissipation Capacitance (Note 6) | 15                                      | pF |

<sup>6.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

# **NOISE CHARACTERISTICS** (Input $t_r = t_f = 3.0 \text{ns}$ , $C_L = 50 \text{pF}$ , $V_{CC} = 5.0 \text{V}$ )

|                  |  | T <sub>A</sub> = 25°C |      |      |
|------------------|--|-----------------------|------|------|
| Symbol           | Characteristic                               | Тур                   | Max  | Unit |
| V <sub>OLP</sub> | Quiet Output Maximum Dynamic V <sub>OL</sub> | 0.8                   | 1.0  | V    |
| V <sub>OLV</sub> | Quiet Output Minimum Dynamic V <sub>OL</sub> | -0.8                  | -1.0 | V    |
| V <sub>IHD</sub> | Minimum High Level Dynamic Input Voltage     |                       | 2.0  | V    |
| V <sub>ILD</sub> | Maximum Low Level Dynamic Input Voltage      |                       | 0.8  | V    |

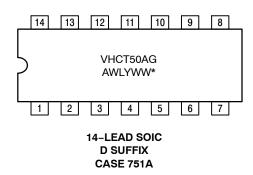
# **ORDERING INFORMATION**

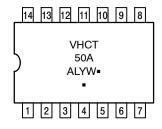
| Device           | Package              | Shipping <sup>†</sup> |  |
|------------------|----------------------|-----------------------|--|
| MC74VHCT50ADR2G  | SOIC-14<br>(Pb-Free) | 2500 / Tape & Reel    |  |
| MC74VHCT50ADTR2G | TSSOP-14             | 0500 / Tono 9 Dool    |  |
| NLVVHCT50ADTR2G* | (Pb-Free)            | 2500 / Tape & Reel    |  |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **MARKING DIAGRAMS**

(Top View)





14-LEAD TSSOP DT SUFFIX CASE 948G

A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

 ${}^{\star}\text{See}$  Applications Note #AND8004/D for date code and traceability information.

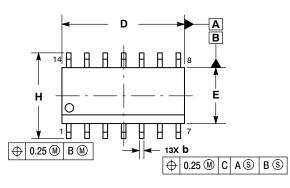
<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

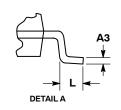


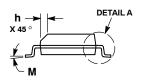


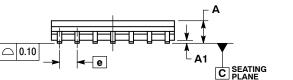
SOIC-14 NB CASE 751A-03 ISSUE L

**DATE 03 FEB 2016** 





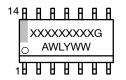




- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - ASME Y14.5M, 1994.
    CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
  DIMENSIONS D AND E DO NOT INCLUDE
  MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

|     | MILLIN | IETERS | INCHES    |       |  |
|-----|--------|--------|-----------|-------|--|
| DIM | MIN    | MAX    | MIN       | MAX   |  |
| Α   | 1.35   | 1.75   | 0.054     | 0.068 |  |
| A1  | 0.10   | 0.25   | 0.004     | 0.010 |  |
| АЗ  | 0.19   | 0.25   | 0.008     | 0.010 |  |
| b   | 0.35   | 0.49   | 0.014     | 0.019 |  |
| D   | 8.55   | 8.75   | 0.337     | 0.344 |  |
| Е   | 3.80   | 4.00   | 0.150     | 0.157 |  |
| е   | 1.27   | BSC    | 0.050 BSC |       |  |
| Н   | 5.80   | 6.20   | 0.228     | 0.244 |  |
| h   | 0.25   | 0.50   | 0.010     | 0.019 |  |
| Ĺ   | 0.40   | 1.25   | 0.016     | 0.049 |  |
| М   | 0 °    | 7°     | 0 °       | 7°    |  |

# **GENERIC MARKING DIAGRAM\***

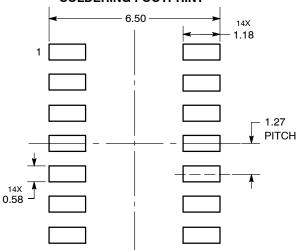


XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

# **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

# **STYLES ON PAGE 2**

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| DESCRIPTION:     | SOIC-14 NB  |  | PAGE 1 OF 2 |  |  |

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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

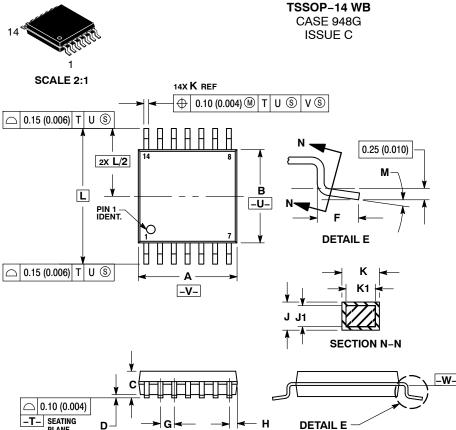
# SOIC-14 CASE 751A-03 ISSUE L

# DATE 03 FEB 2016

| STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE | STYLE 2:<br>CANCELLED   | STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE  | STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE  |
|---|---|---|---|
| STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE | STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE | STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE | STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE |

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|------------------|-------------|--|-------------|--|--|
| DESCRIPTION:     | SOIC-14 NB  |  | PAGE 2 OF 2 |  |  |

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**DATE 17 FEB 2016** 

- NOTES.

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

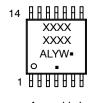
  3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY
- REFERENCE ONLY.
  DIMENSION A AND B ARE TO BE
  DETERMINED AT DATUM PLANE -W-.

|     | MILLIMETERS |      | INCHES    |       |
|-----|-------------|------|-----------|-------|
| DIM | MIN         | MAX  | MIN       | MAX   |
| Α   | 4.90        | 5.10 | 0.193     | 0.200 |
| В   | 4.30        | 4.50 | 0.169     | 0.177 |
| С   | -           | 1.20 |           | 0.047 |
| D   | 0.05        | 0.15 | 0.002     | 0.006 |
| F   | 0.50        | 0.75 | 0.020     | 0.030 |
| G   | 0.65        | BSC  | 0.026     | BSC   |
| Н   | 0.50        | 0.60 | 0.020     | 0.024 |
| J   | 0.09        | 0.20 | 0.004     | 0.008 |
| J1  | 0.09        | 0.16 | 0.004     | 0.006 |
| K   | 0.19        | 0.30 | 0.007     | 0.012 |
| K1  | 0.19        | 0.25 | 0.007     | 0.010 |
| L   | 6.40 BSC    |      | 0.252 BSC |       |
| М   | ° o         | 8 °  | 0 °       | 8 °   |

# **GENERIC MARKING DIAGRAM\***



= Assembly Location

= Wafer Lot V = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

| 0.10 (0.004)  T— SEATING PLANE D  G  G   | → H DETAIL E  |
|--|---------------|
| SOLDERING  | FOOTPRINT     |
| 7. 1 1 1 1 1 1 1 1 1 1 2 6 1 1 1 2 6 1 | 0.65<br>PITCH |

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|------------------|-------------|---|-------------|--|
| DESCRIPTION:     | TSSOP-14 WB |   | PAGE 1 OF 1 |  |

**DIMENSIONS: MILLIMETERS** 

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